



# STRUCTURAL AND MORPHOLOGICAL PROPERTIES OF ELECTRODEPOSITED BISMUTH TELLURIDE ( $\text{Bi}_2\text{Te}_3$ ) THIN FILMS

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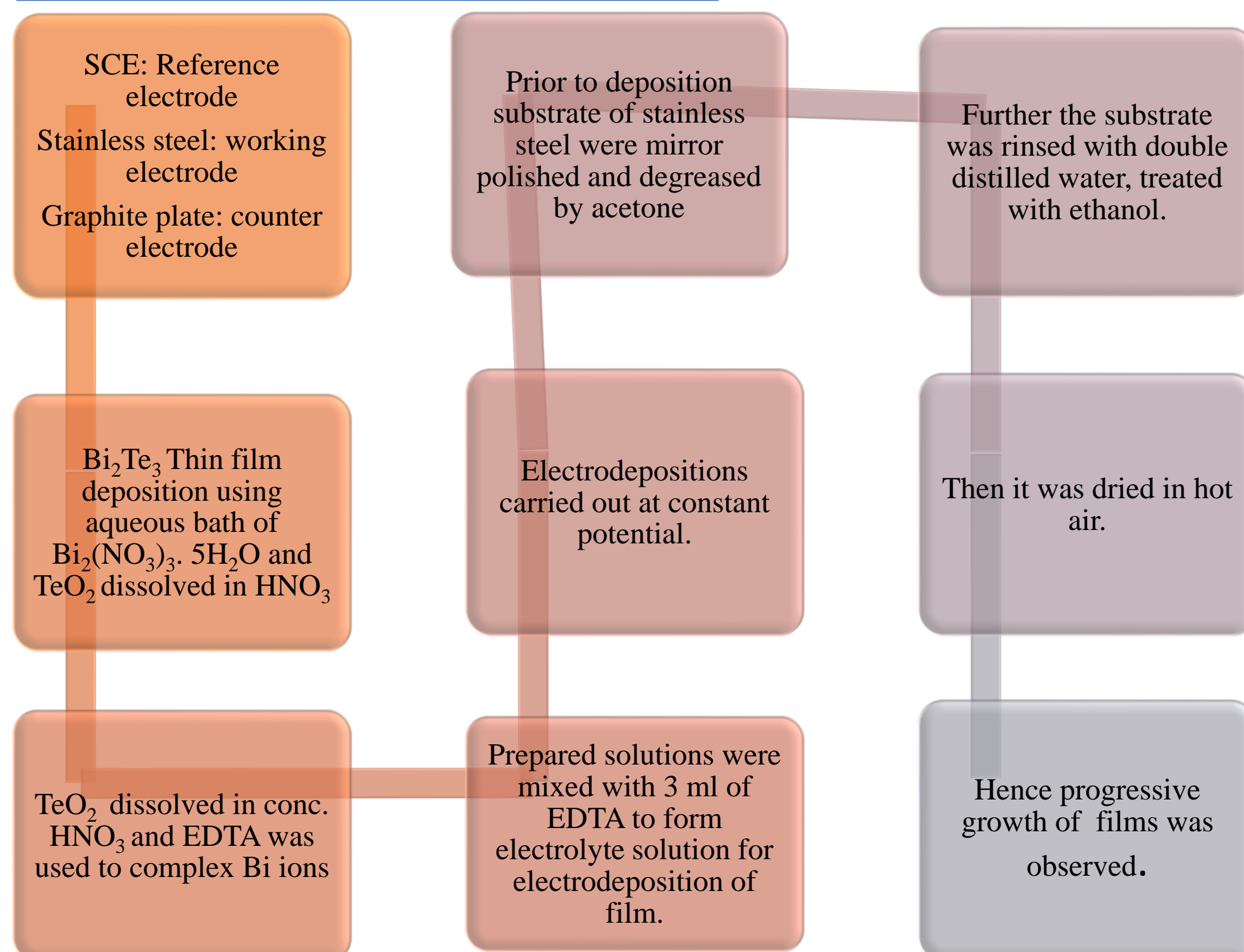
## ABSTRACT:

Present work deals with the electrodeposition of  $\text{Bi}_2\text{Te}_3$  thin films. Structural, elemental and morphological analysis of deposited films have been carried out using XRD and SEM with EDXS technique. XRD confirms the formation of  $\text{Bi}_2\text{Te}_3$  crystals with crystalline size in the range of 5 to 9 nm. EDXs is in agreement with X-Ray diffractometer and confirms the qualitative formation of  $\text{Bi}_2\text{Te}_3$  in stoichiometry of 2:3. Scanning electron micrograph reveals the uniform spherical morphology for the deposited films.

## INTRODUCTION:

Bismuth telluride is attractive material due to its efficiency of conversion of heat into electricity [1]. Currently, bunch of research is going on to improve the efficiency of thermoelectric materials by the development of  $\text{Bi}_2\text{Te}_3$  nanostructure.  $\text{Bi}_2\text{Te}_3$  is basically considered as a compound element of bismuth and tellurium when bismuth is alloyed with tellurium, then it behaves as a well organized semiconductor thermoelectric type material [2]. It is used for some applications like cooler thermoelectric refrigeration, thermal sensor, TEG, etc [3]. In this sense, in present work attempt is made for preparation of Bismuth telluride thin films by electrodeposition technique. Preparative parameter like deposition time, thickness of films, deposition potential, are optimized. Thin film of  $\text{Bi}_2\text{Te}_3$  is characterized by XRD, SEM, EDAX.

## EXPERIMENTAL DETAILS:



## SEM STUDIES OF $\text{Bi}_2\text{Te}_3$ THIN FILM:

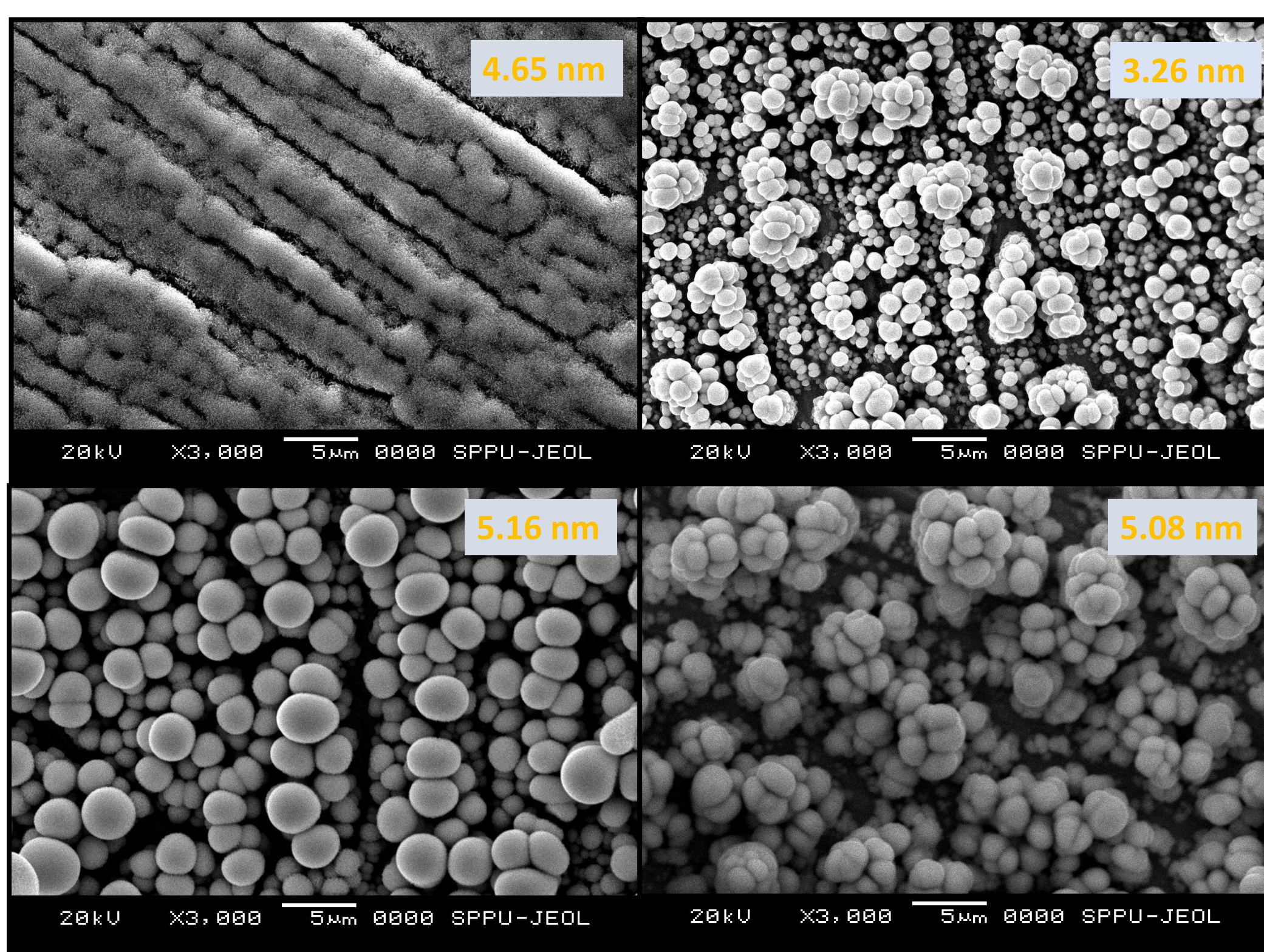


FIGURE: SCANNING ELECTRON MICROGRAPH OF THE DEPOSITED  $\text{Bi}_2\text{Te}_3$  THIN FILM

Time [min]	2 theta [°]	Crystal size [nm]	Microstrain $\epsilon = \beta \cos \theta / 4$ ( $10^{-4} \text{ lin}^{-2} \text{ m}^{-4}$ )	Dislocation density $\delta = 15 \epsilon / aD$ ( $10^{14} \text{ lin}/\text{m}^2$ )
20	27.72	4.65	77.82	573.08
30	27.58	3.26	111.07	1167.33
40	27.70	5.16	70.07	464.63
50	27.56	5.08	71.24	480.21

TABLE : CHARACTERISTICS OF DEPOSITED FILMS

## REFERENCES:

- [1] D.M. ROWE, CRC handbook of thermoelectrics. CRC press, 1995.
- [2] H. Zou, D. M. Rowe, and G. Min, "Preparation and characterization of p-type  $\text{Sb}_2\text{Te}_3$  and n-type  $\text{Bi}_2\text{Te}_3$  thin films grown by coevaporation," J. Vac. Sci. Technol. A Vacuum, Surfaces, Film., vol. 19, no. 3, pp. 899–903, May 2001.
- [3] T. M. Tritt, "Science's," vol. 283, no. February, pp. 4–5, 1999.

## WORKING PRINCIPLE:

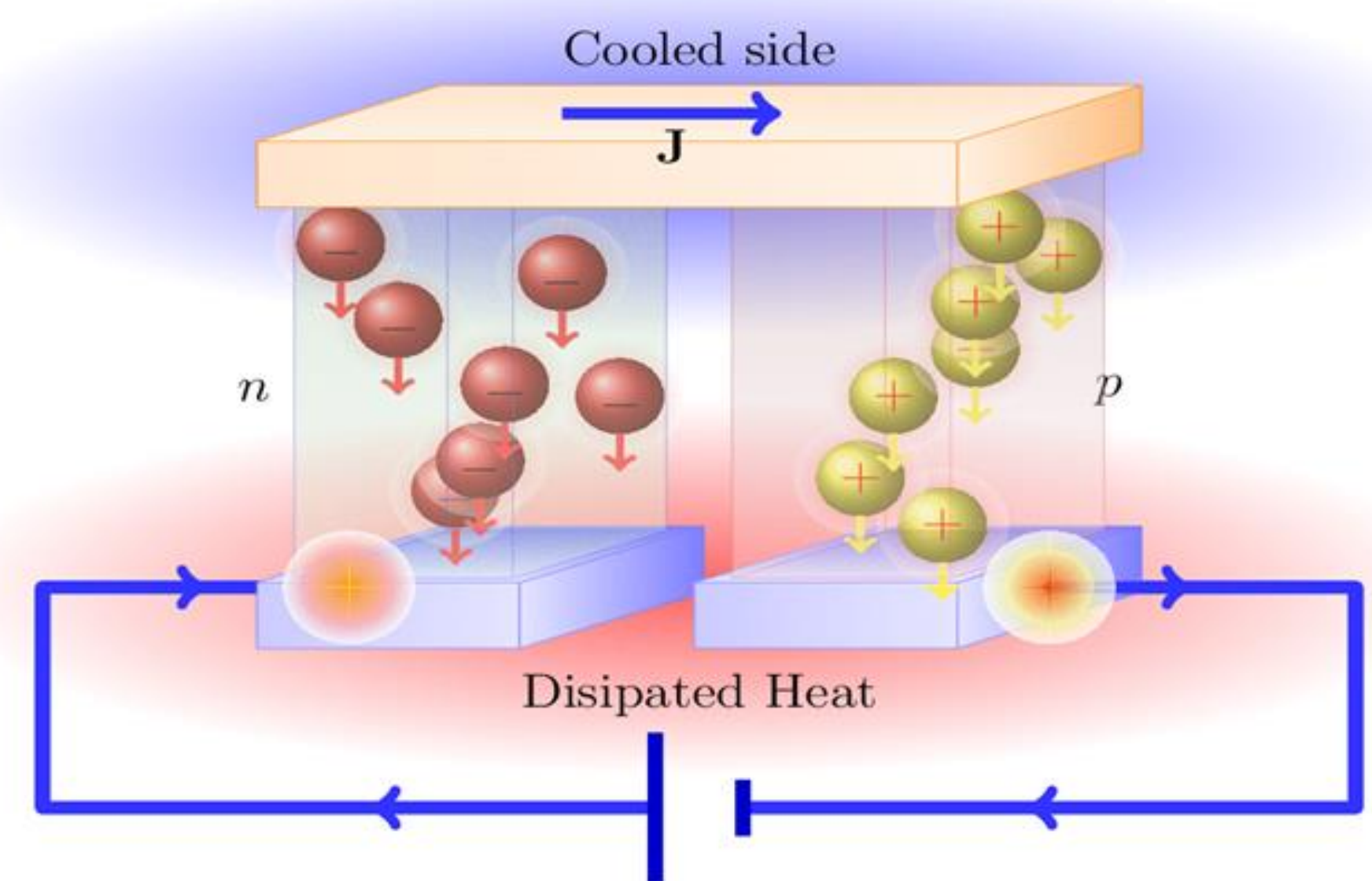


FIGURE: PELTIER EFFECT IN THERMOELECTRICS

## RESULTS AND DISCUSSION:

### XRD ANALYSIS:

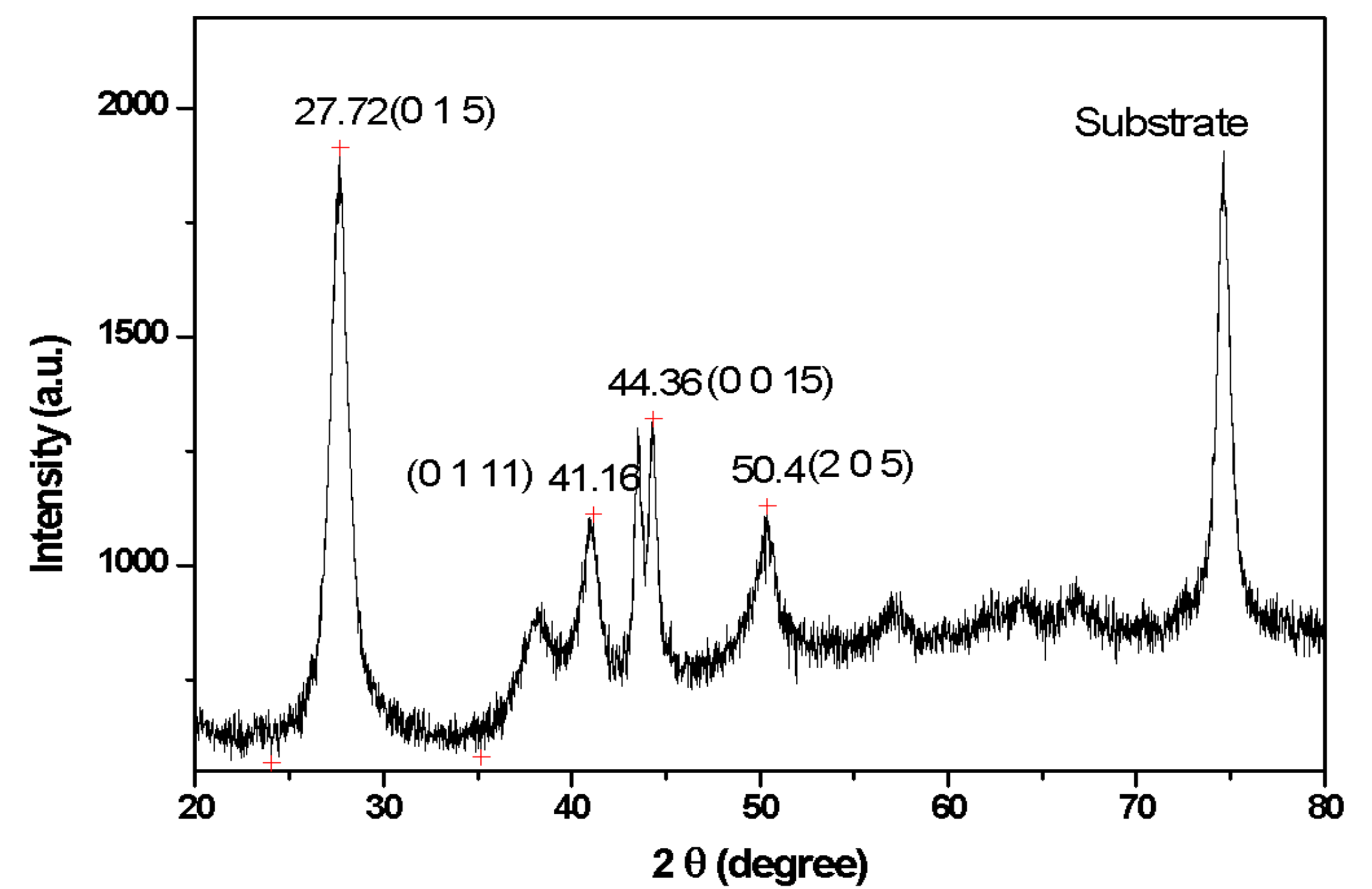


FIGURE: X-RAY PATTERN OF  $\text{Bi}_2\text{Te}_3$  THIN FILM.

### EDAX ANALYSIS:

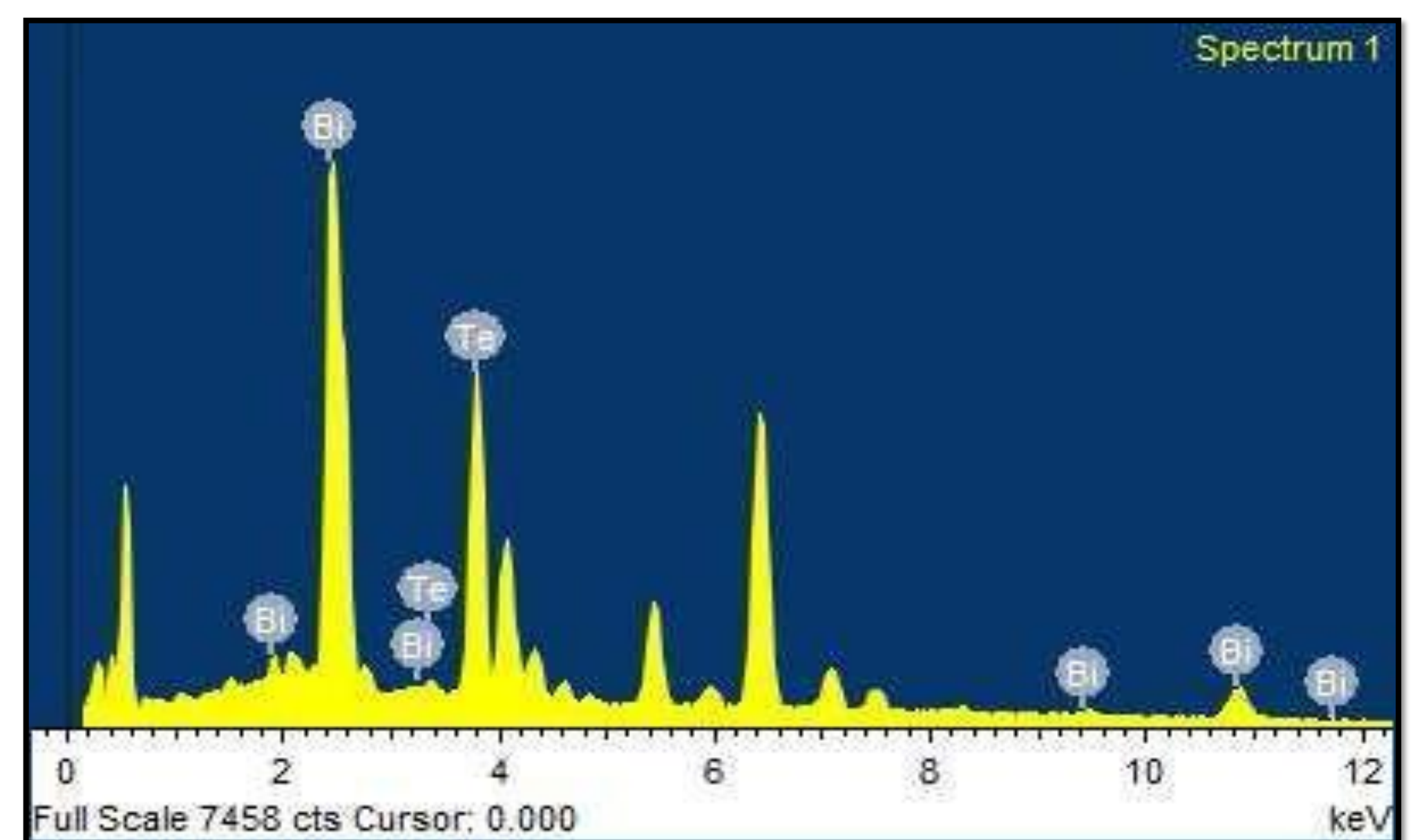


FIGURE: ELEMENTAL ANALYSIS OF  $\text{Bi}_2\text{Te}_3$  THIN FILMS

## CONCLUSION:

- Successful deposition of  $\text{Bi}_2\text{Te}_3$  is observed.
- XRD reveals Rhombohedral structure of deposited films, the crystal size observed was between 3.26 nm to 5.16 nm.
- Elemental analysis qualitatively supports XRD.
- SEM studies declare that thin film of  $\text{Bi}_2\text{Te}_3$  has marigold/ cauliflower morphology.
- Hence, the work concludes that  $\text{Bi}_2\text{Te}_3$  thin films are promising for thermoelectric applications.

## AKNOWLEDGEMENT:

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